

## Super Barrier Rectifier ™

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
I <sub>F(AV)</sub> Rectangular Waveform	60	Α
$V_{RRM}$	150	V
V <sub>F</sub> @30A, Tj=125 <sup>O</sup> C	0.73	V, typ
Tj (operating/storage)	-65 to 175	°C

## **ELECTRICAL:**

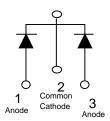
- \* Low Forward Voltage Drop
- \* Reliable High Temperature Operation
- \* Super Barrier Design
- \* Softest, fast switching capability
- \* 175°C Operating Junction Temperature

Device optimized for low forward voltage drop to maximize efficiency in Power Supply applications

## MECHANICAL:

\* Molded Plastic TO-220 package





Maximum Ratings and Electrical Characteristics (at 25°C unless otherwise specified)						
20	SYMBOL			UNITS		
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	$egin{array}{c} egin{array}{c} egin{array}{c} V_{RM} \ egin{array}{c} V_{RRM} \end{array}$	150		Volts		
Average Rectified Forward Current (Rated V <sub>R</sub> -20Khz Square Wave) - 50% duty cycle	I <sub>o</sub>	60		Amps		
Peak Forward Surge Current - 1/2 60hz	I <sub>FSM</sub>	350		Amps		
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I <sub>RRM</sub>	3		Amps		
Instantaneous Forward Voltage (per leg) $I_F = 30A$ ; $T_J = 25^{\circ}C$ $I_F = 30A$ ; $T_J = 125^{\circ}C$	V <sub>F</sub>	Typ  	Max 0.93 0.77	Volts		
Maximum Instantaneous Reverse Current at Rated $V_{RM}$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I <sub>R</sub> *	Typ  	Max 100 10	uA mA		
Maximum Rate of Voltage Change (at Rated $V_R$ )	dv/dt	10,000		V/uS		
Maximum Thermal Resistance JC (per leg)	$R\theta_{JC}$	2		°C/W		
Operating and Storage Junction Temperature	TJ	-65 to +175		°C		

<sup>\*</sup> Pulse width < 300 uS, Duty cycle < 2%

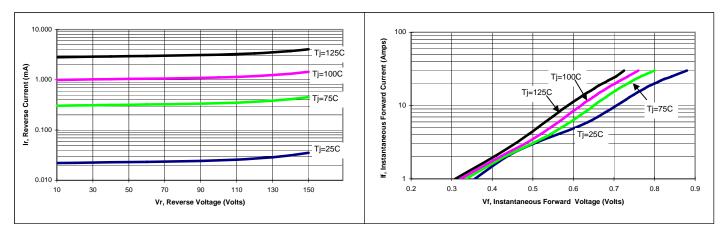


Figure 1: Typical Reverse Current (per leg)

Figure 2: Typical Forward Voltage (per leg)

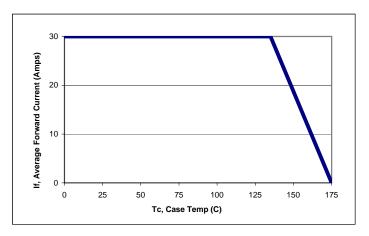


Figure 3: Current Derating, Case (per leg)

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